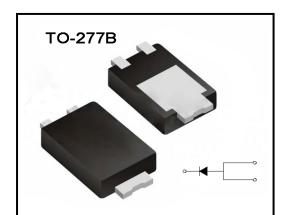


Package

Schottky Barrier Diode

Features

- · Excellent high temperature stability
- · Low forward voltage
- · Low power loss/ high efficiency
- · High forward surge capability
- · Ideal for automated placement
- Compliant to RoHS Directive 2011/65/EU and in accor-dance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



Applications

The Schottky barrier rectifier is designed for high frequency miniature switched mode power supplies such as adapters, lighting and on-board DC/DC converters.

Mechanical Data

- Case: TO-277B
- · Polarity: Indicated by cathode band
- Moisture sensitivity level: level 1, per J-STD-020
- · Molding compound meets UL 94 V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per JESD22-B102 Meet JESD 201 class 2 whisker test
- Weight: 0.095g (appr oximately)

Marking

BORN QXYY SB1545L

Ordering information

Order code	Package	Base qty	Delivery mode
NSB1545L	TO-277B	5K	Tape and Reel

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Schottky Barrier Diode

Maximum Ratings (@T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	45	V
I _{F(AV)}	Maximum Average Forward Rectified Current	15	А
I _{FSM}	Peak forward surge current 8.3ms single half	250	А
	sine-wave superimposed on rated load per diode	230	
V _F	Maximum instantaneous forward voltage	0.50	V
	per diode (Note1) @I _F =15A	0.50	
I _R	Maximum instantaneous reverse current	150	uA
	per diode at rated reverse voltage	130	
$R_{ hetaJL}$	Typical thermal resistance	11	°C/W
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to +150	°C
	Range	-55 (0 + 150	

Note 1: Pulse Test with Pulse Width=300µs, 1% Duty Cycle.





Schottky Barrier Diode

Typical Performance Characteristics (T_A = 25 $^{\circ}$ C, unless otherwise noted)

Figure 1: Forward Current Derating Curve

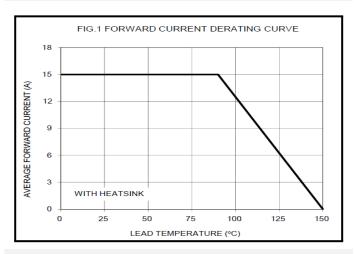


Figure 3: Max. Non-Repetive Forward Surge Current

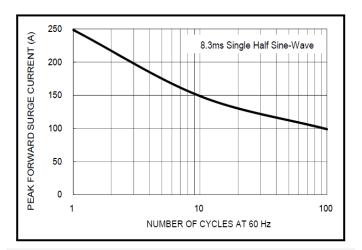


Figure 5: Typical Junction Capacitance

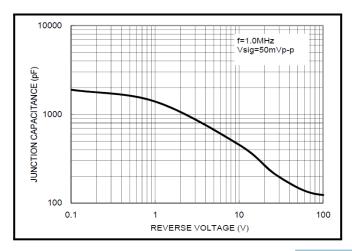


Figure 2: Typical Forward Characteristics

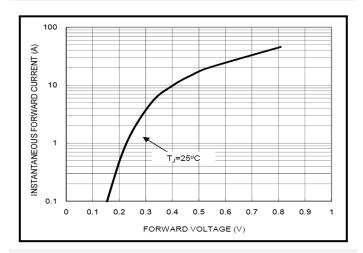
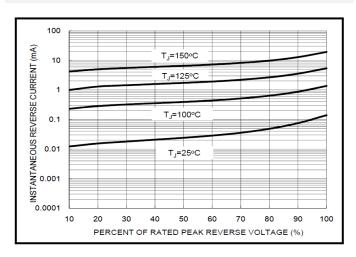


Figure 4: Typical Reverse Characteristics



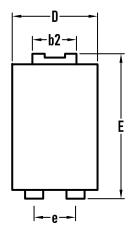
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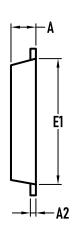


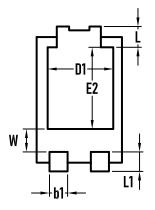


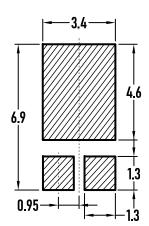
Schottky Barrier Diode

Outline Drawing - TO-277B









OVMDOL	MILLIMETER		
SYMBOL	MIN.	MAX.	
А	1.05	1.2	
A2	0.25	0.4	
b1	0.8	1.0	
b2	1.7	1.9	
D	4.1	4.3	
D1	3.0	3.3	
E	6.4	6.6	
е	1.86		
E1	5.6	5.8	
E2	3.52		
L	0.68	0.88	
L1	0.85	1.1	
W	1.1	1.4	